

MOSFET - Power, Single, P-Channel, TSOP-6 -30 V, -4.7 A NTGS4111P, NVGS4111P

Features

- Leading -30 V Trench Process for Low $R_{DS(on)}$
- Low Profile Package Suitable for Portable Applications
- Surface Mount TSOP-6 Package Saves Board Space
- Improved Efficiency for Battery Applications
- NV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- Pb-Free Package is Available

Applications

- Battery Management and Switching
- Load Switching
- Battery Protection

MAXIMUM RATINGS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)

Rating			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	−30	V
Gate-to-Source Voltage			V _{GS}	±20	V
Continuous Drain Current (Note 1)	Steady State	T _A = 25 °C	I _D	−3.7	A
		T _A = 85 °C		−2.7	
	t ≤ 5 s	T _A = 25 °C		−4.7	
Power Dissipation (Note 1)	Steady State	T _A = 25 °C	P _D	1.25	W
	t ≤ 5 s			2.0	
Continuous Drain Current (Note 2)	Steady State	T _A = 25 °C	I _D	−2.6	A
		T _A = 85 °C		−1.9	
Power Dissipation (Note 2)		T _A = 25 °C	P _D	0.63	W
Pulsed Drain Current	tp = 10 μs		I _{DM}	−15	A
Operating Junction and Storage Temperature			T _J , T _{STG}	−55 to 150	°C
Source Current (Body Diode)			I _S	−1.7	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C

THERMAL RESISTANCE RATINGS

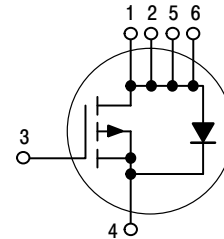
Rating	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	100	$^{\circ}\text{C/W}$
Junction-to-Ambient - $t \leq 5\text{ s}$ (Note 1)	$R_{\theta JA}$	62.5	
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	200	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

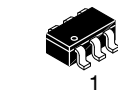
1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).
2. Surface-mounted on FR4 board using the minimum recommended pad size (Cu area = 0.006 in sq).

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
-30 V	38 m Ω @ -10 V	-4.7 A
	68 m Ω @ -4.5 V	

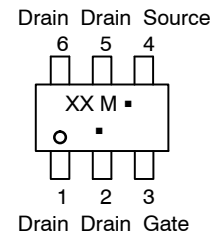
P-Channel



MARKING DIAGRAM & PIN ASSIGNMENT



TSOP-6
CASE 318G
STYLE 1



- XX = Specific Device Code
- M = Date Code*
- = Pb-Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note [AND8002/D](#).

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 5.

NTGS4111P, NVGS4111P

ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			-17		mV/ $^{\circ}\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = -24\text{ V}$	$T_J = 25\text{ }^{\circ}\text{C}$		-1.0	μA
			$T_J = 125\text{ }^{\circ}\text{C}$		-100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\text{ }\mu\text{A}$	-1.0		-3.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			5.0		mV/ $^{\circ}\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -3.7\text{ A}$		38	60	$\text{m}\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -2.7\text{ A}$		68	110	
Forward Transconductance	g_{FS}	$V_{DS} = -10\text{ V}, I_D = -3.7\text{ A}$		6.0		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = -15\text{ V}$		750		pF
Output Capacitance	C_{OSS}			140		
Reverse Transfer Capacitance	C_{RSS}			105		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -10\text{ V}, V_{DD} = -15\text{ V}, I_D = -3.7\text{ A}$		15.25	32	nC
Threshold Gate Charge	$Q_{G(TH)}$			0.8		
Gate-to-Source Charge	Q_{GS}			2.6		
Gate-to-Drain Charge	Q_{GD}			3.4		

SWITCHING CHARACTERISTICS, $V_{GS} = -10\text{ V}$ (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -10\text{ V}, V_{DD} = -15\text{ V}, I_D = -1.0\text{ A}, R_G = 6.0\text{ }\Omega$		9.0	17	ns
Rise Time	t_r			9.0	18	
Turn-Off Delay Time	$t_{d(OFF)}$			38	85	
Fall Time	t_f			22	45	

SWITCHING CHARACTERISTICS, $V_{GS} = -4.5\text{ V}$ (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5\text{ V}, V_{DD} = -15\text{ V}, I_D = -1.0\text{ A}, R_G = 6.0\text{ }\Omega$		11	20	ns
Rise Time	t_r			15	28	
Turn-Off Delay Time	$t_{d(OFF)}$			28	56	
Fall Time	t_f			22	50	

DRAIN - SOURCE DIODE CHARACTERISTICS

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Forward Diode Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_S = -1.0\text{ A}$	$T_J = 25\text{ }^{\circ}\text{C}$	-0.76	-1.2	V
			$T_J = 125\text{ }^{\circ}\text{C}$	-0.60		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = -1.0\text{ A}$		17	40	ns
Charge Time	t_a			9.0		
Discharge Time	t_b			8.0		
Reverse Recovery Charge	Q_{RR}			8.0		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

4. Switching characteristics are independent of operating junction temperatures.

NTGS4111P, NVGS4111P

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

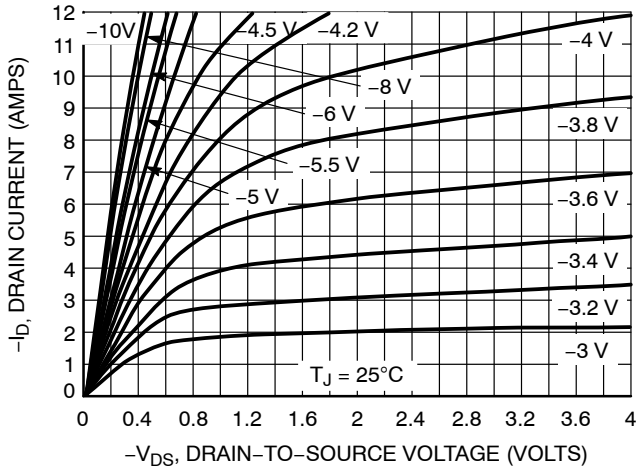


Figure 1. On-Region Characteristics

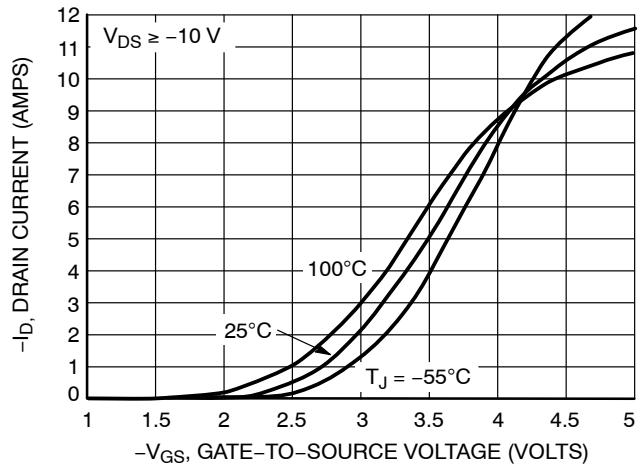


Figure 2. Transfer Characteristics

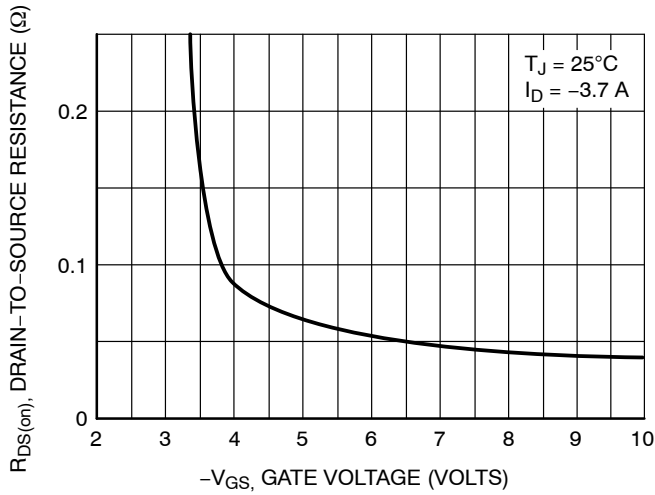


Figure 3. On-Resistance vs. Gate-to-Source Voltage

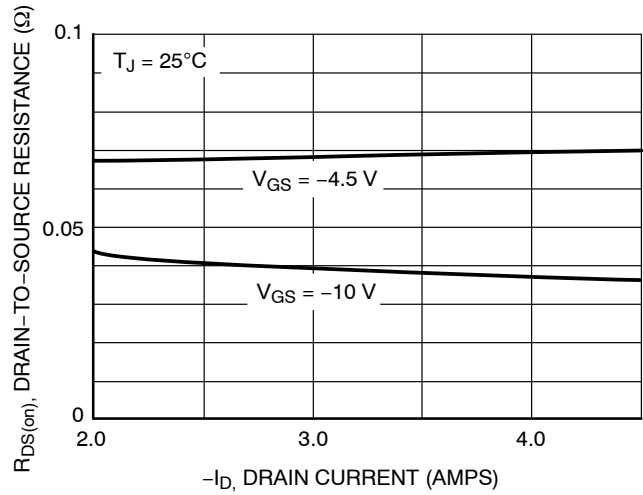


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

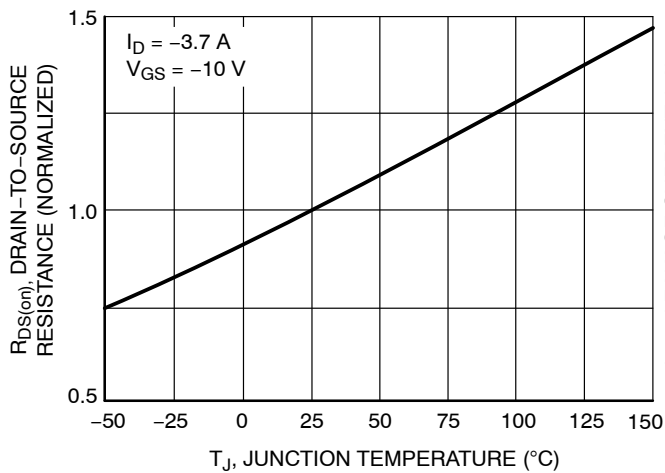


Figure 5. On-Resistance Variation with Temperature

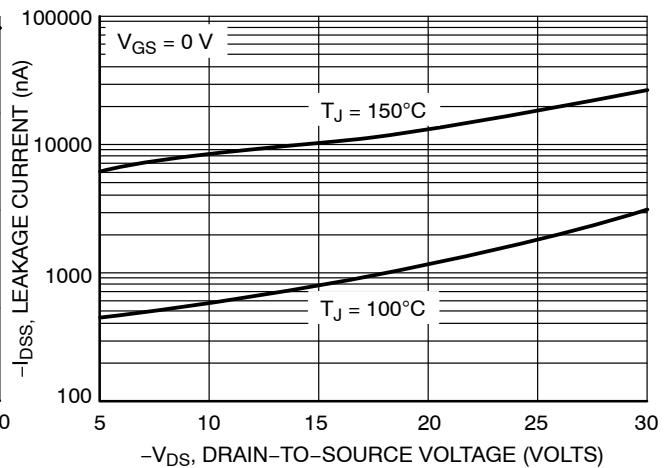
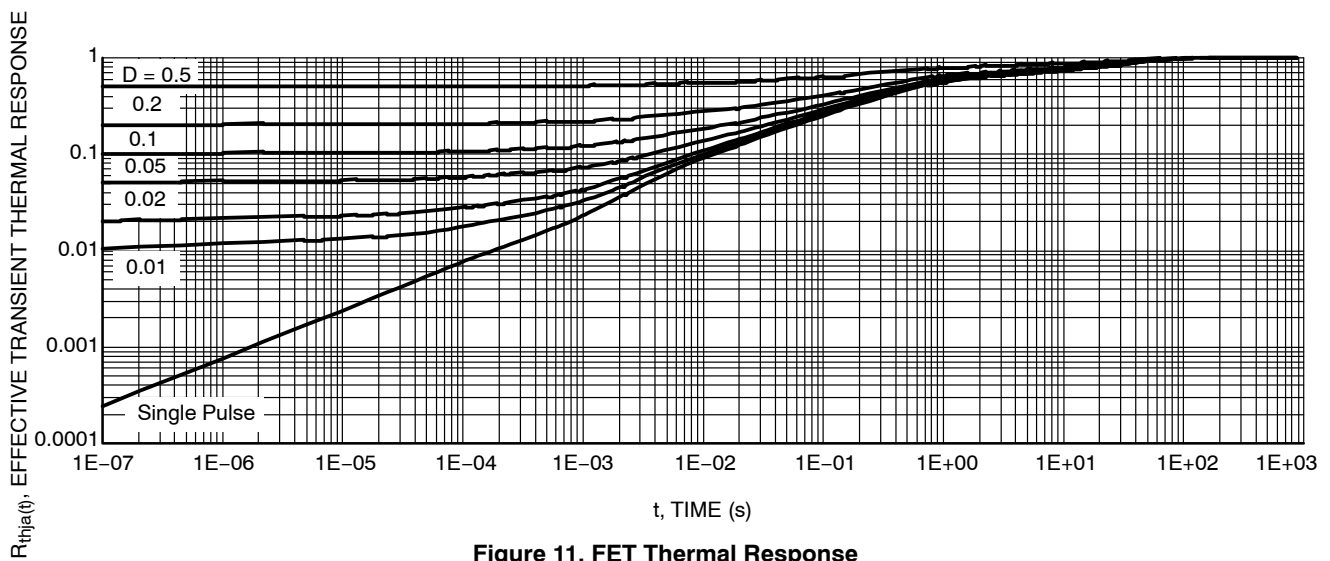
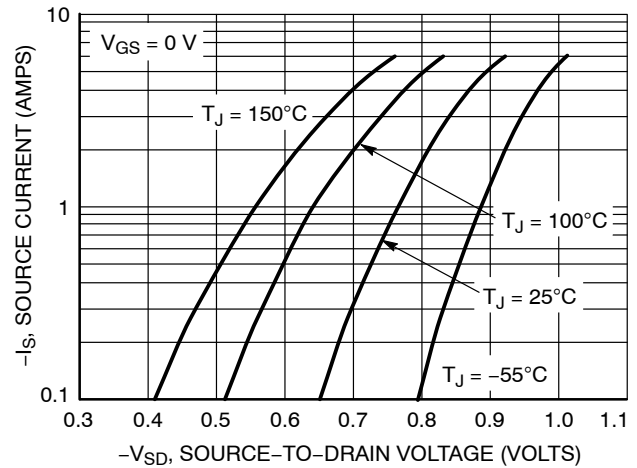
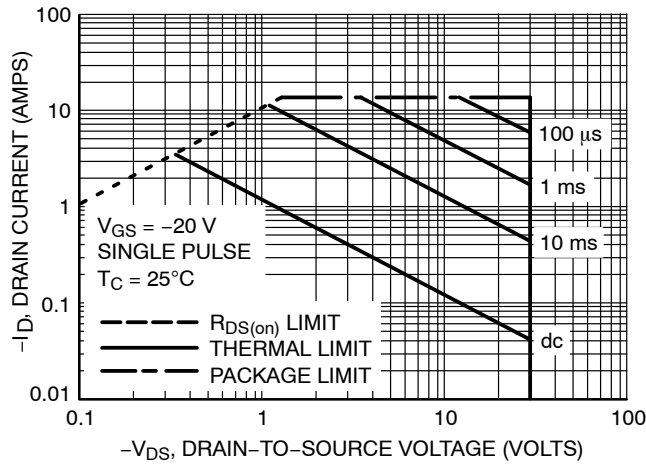
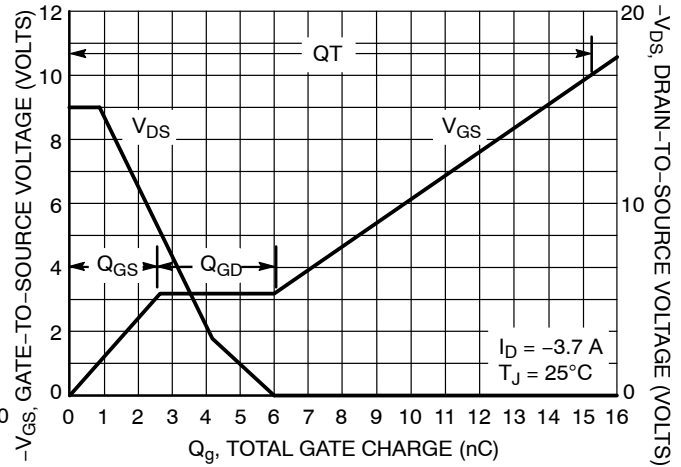
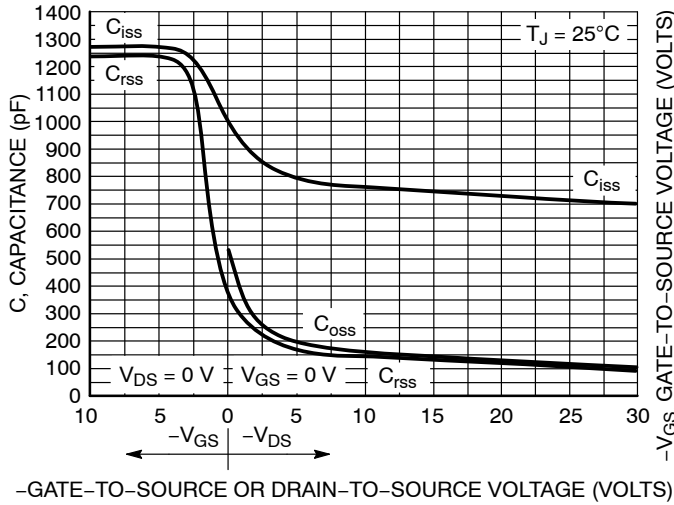


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTGS4111P, NVGS4111P

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)



NTGS4111P, NVGS4111P

Table 1. ORDERING INFORMATION

Part Number	Marking (XX)	Package	Shipping [†]
NTGS4111PT1G	TG	SC-88 (Pb-Free)	3000 / Tape & Reel
NVGS4111PT1G	VTG	SC-88 (Pb-Free)	3000 / Tape & Reel

DISCONTINUED (Note 5)

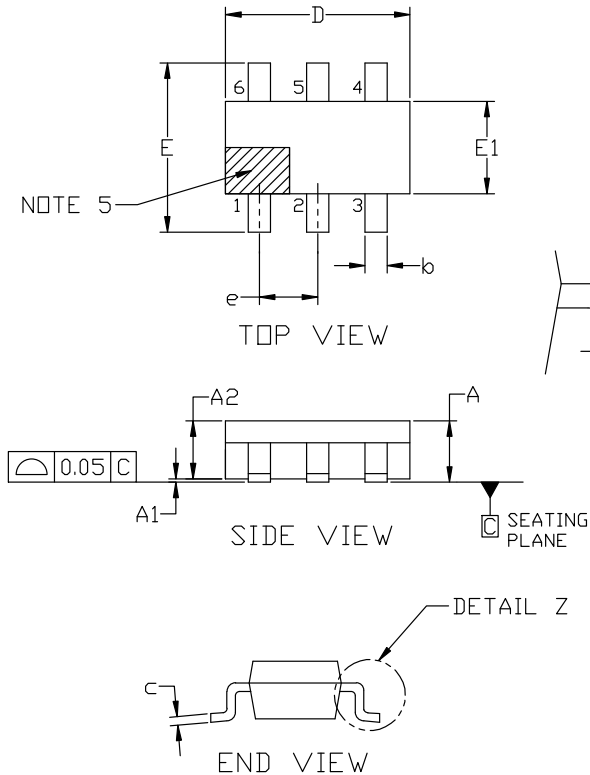
NTGS4111PT1	TG	SC-88	3000 / Tape & Reel
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[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

5. **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.

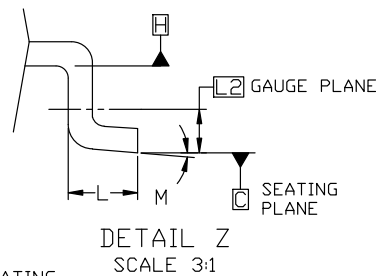

TSOP-6 3.00x1.50x0.90, 0.95P
CASE 318G
ISSUE W

DATE 26 FEB 2024

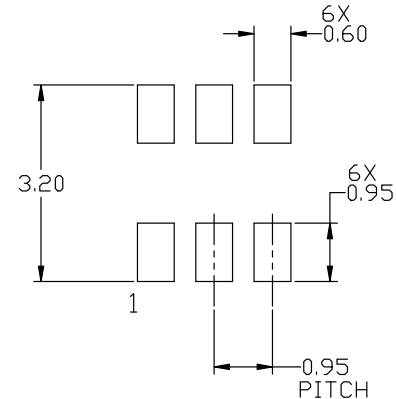


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
5. PIN 1 INDICATOR MUST BE LOCATED IN THE INDICATED ZONE



MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.01	0.06	0.10
A2	0.80	0.90	1.00
b	0.25	0.38	0.50
c	0.10	0.18	0.26
D	2.90	3.00	3.10
E	2.50	2.75	3.00
E1	1.30	1.50	1.70
e	0.85	0.95	1.05
L	0.20	0.40	0.60
L2	0.25 BSC		
M	0°	---	10°


RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

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TSOP-6 3.00x1.50x0.90, 0.95P
CASE 318G
ISSUE W

DATE 26 FEB 2024

GENERIC
MARKING DIAGRAM*



IC



STANDARD

XXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
■ = Pb-Free Package

XXX = Specific Device Code
M = Date Code
■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 2: PIN 1. EMITTER 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. BASE 2 6. COLLECTOR 2	STYLE 3: PIN 1. ENABLE 2. N/C 3. R BOOST 4. Vz 5. V in 6. V out	STYLE 4: PIN 1. N/C 2. V in 3. NOT USED 4. GROUND 5. ENABLE 6. LOAD	STYLE 5: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 6: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR
STYLE 7: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. N/C 5. COLLECTOR 6. EMITTER	STYLE 8: PIN 1. Vbus 2. D(in) 3. D(in)+ 4. D(out)+ 5. D(out) 6. GND	STYLE 9: PIN 1. LOW VOLTAGE GATE 2. DRAIN 3. SOURCE 4. DRAIN 5. DRAIN 6. HIGH VOLTAGE GATE	STYLE 10: PIN 1. D(OUT)+ 2. GND 3. D(OUT)- 4. D(IN)- 5. VBUS 6. D(IN)+	STYLE 11: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1/GATE 2	STYLE 12: PIN 1. I/O 2. GROUND 3. I/O 4. I/O 5. VCC 6. I/O
STYLE 13: PIN 1. GATE 1 2. SOURCE 2 3. GATE 2 4. DRAIN 2 5. SOURCE 1 6. DRAIN 1	STYLE 14: PIN 1. ANODE 2. SOURCE 3. GATE 4. CATHODE/DRAIN 5. CATHODE/DRAIN 6. CATHODE/DRAIN	STYLE 15: PIN 1. ANODE 2. SOURCE 3. GATE 4. DRAIN 5. N/C 6. CATHODE	STYLE 16: PIN 1. ANODE/CATHODE 2. BASE 3. EMITTER 4. COLLECTOR 5. ANODE 6. CATHODE	STYLE 17: PIN 1. EMITTER 2. BASE 3. ANODE/CATHODE 4. ANODE 5. CATHODE 6. COLLECTOR	

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